

Abstract

Semiconductor wafer made of single-crystal silicon and process for the production thereof

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A semiconductor wafer made of single-crystal silicon which comprises certain concentrations of oxygen, nitrogen and hydrogen; the semiconductor wafer further comprises:

10 BMD seeds having a density meaned over the radius of not less than $1 \times 10^5 \text{ cm}^{-3}$ and not more than $1 \times 10^7 \text{ cm}^{-3}$;

surface defects having a density meaned over the radius of not less than 1100 cm^{-2} ; and

BMDs, whose density is not lower than a lower limit of $5 \times 10^8 / \text{cm}^3$.

15 The invention likewise provides a process for producing a semiconductor wafer made of single-crystal silicon.

Drawing relating to abstract: Fig. 1